Monolithic N-Channel JFET Duals

SST404 U401 U406
SST406 U404

PRODUCT SUMMARY					
Part Number	**$V_{GS(off)}$ (V)**	**$V_{(BR)GSS}$ Min (V)**	**g_{fs} Min (mS)**	**I_G Typ (pA)**	**$\|V_{GS1} - V_{GS2}\|$ Max (mV)**
U401	–0.5 to –2.5	–40	1	–2	5
SST/U404	–0.5 to –2.5	–40	1	–2	15
SST/U406	–0.5 to –2.5	–40	1	–2	40

FEATURES

- Monolithic Design
- High Slew Rate
- Low Offset/Drift Voltage
- Low Gate Leakage: 2 pA
- Low Noise
- High CMRR: 102 dB

BENEFITS

- Tight Differential Match vs. Current
- Improved Op Amp Speed, Settling Time Accuracy
- Minimum Input Error/Trimming Requirement
- Insignificant Signal Loss/Error Voltage
- High System Sensitivity
- Minimum Error with Large Input Signal

APPLICATIONS

- Wideband Differential Amps
- High-Speed,Temp-Compensated, Single-Ended Input Amps
- High-Speed Comparators
- Impedance Converters

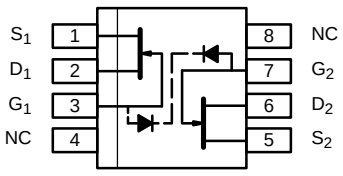
DESCRIPTION

The SST/U401 series of high-performance monolithic dual JFETs features extremely low noise, tight offset voltage and low drift over temperature specifications, and is targeted for use in a wide range of precision instrumentation applications. This series has a wide selection of offset and drift specifications with the U401 featuring a 5-mV offset and 10-μV/°C drift.

The U series, hermetically sealed TO-71 package is available with full military processing (see Military Information). The SST series SO-8 package provides ease of manufacturing, and the symmetrical pinout prevents improper orientation. The SO-8 package is available with tape-and-reel options for compatibility with automatic assembly methods (see Packaging Information).

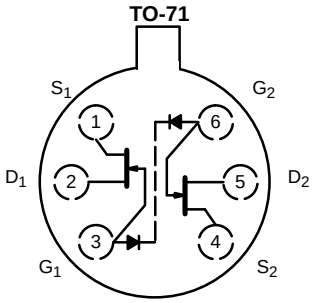
For similar high-gain products in TO-78 packaging, see the 2N5911/5912 data sheet.

Narrow Body SOIC



Top View
SST404, SST406

TO-71



Top View
U401, U404, U406

ABSOLUTE MAXIMUM RATINGS

Gate-Drain, Gate-Source Voltage . . . . . –40 V
Gate Current . . . . . 10 mA
Lead Temperature ($^1/_{16}$" from case for 10 sec.) . . . . . 300°C
Storage Temperature : U Prefix . . . . . –65 to 200°C
SST Prefix . . . . . –55 to 150°C

Operating Junction Temperature . . . . . –55 to 150°C
Power Dissipation : Per Side[a] . . . . . 300 mW
Total[b] . . . . . 500 mW

Notes
a. Derate 2.4 mW/°C above 25°C
b. Derate 4 mW/°C above 25°C

For applications information see AN106.

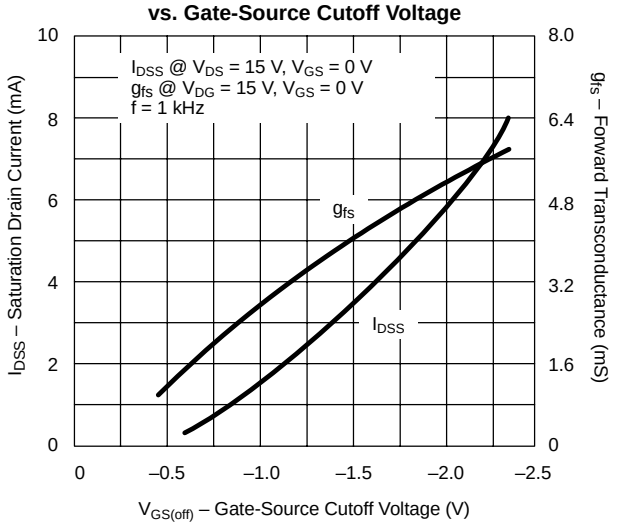
SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Conditions	Typ[a]	Limits U401 Min	Limits U401 Max	Limits SST/U404 Min	Limits SST/U404 Max	Limits SST/U406 Min	Limits SST/U406 Max	Unit
Static										
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	I_G = –1 µA, V_{DS} = 0 V	–58	–40		–40		–40		V
	$V_{(BR)G1-G2}$	I_G = ±1 µA, V_{DS} = 0 V, V_{GS} = 0 V	±45	±30		±30		±30		
Gate-Source Cutoff Voltage	$V_{GS(off)}$	V_{DS} = 15 V, I_D = 1 nA	–1.5	–0.5	–2.5	–0.5	–2.5	–0.5	–2.5	
Saturation Drain Current[b]	I_{DSS}	V_{DS} = 10 V, V_{GS} = 0 V	3.5	0.5	10	0.5	10	0.5	10	mA
Gate Reverse Current	I_{GSS}	V_{GS} = –30 V, V_{DS} = 0 V	–2		–25		–25		–25	pA
		T_A = 125°C	–1							nA
Gate Operating Current	I_G	V_{DG} = 15 V, I_D = 200 µA	–2		–15		–15		–15	pA
		T_A = 125°C	–0.8		–10		–10		–10	nA
Drain-Source On-Resistance	$r_{DS(on)}$	V_{GS} = 0 V, I_D = 0.1 mA	250							Ω
Gate-Source Voltage	V_{GS}	V_{DG} = 15 V, I_D = 200 µA	–1		–2.3		–2.3		–2.3	V
Gate-Source Forward Voltage	$V_{GS(F)}$	I_G = 1 mA , V_{DS} = 0 V	0.7							
Dynamic										
Common-Source Forward Transconductance	g_{fs}	V_{DS} = 15 V, I_D = 200 µA f = 1 kHz	1.5	1	2	1	2	1	2	mS
Common-Source Output Conductance	g_{os}		1.3		2		2		2	µS
Common-Source Forward Transconductance	g_{fs}	V_{DS} = 10 V, V_{GS} = 0 V f = 1 kHz	4	2	7	2	7	2	7	mS
Common-Source Output Conductance	g_{os}		5		30		30		30	µS
Common-Source Input Capacitance	C_{iss}	V_{DS} = 15 V, I_D = 200 µA f = 1 MHz	4		8		8		8	pF
Common-Source Reverse Transfer Capacitance	C_{rss}		1.5		3		3		3	
Equivalent Input Noise Voltage	$\overline{e}_n$	V_{DS} = 15 V, I_D = 200 µA f = 10 Hz	10		20		20		20	$\frac{nV}{\sqrt{Hz}}$
Matching										
Differential Gate-Source Voltage	$\lvert V_{GS1} - V_{GS2} \rvert$	V_{DG} = 10 V, I_D = 200 µA			5		15		40	mV
Gate-Source Voltage Differential Change with Temperature	$\frac{\Delta \lvert V_{GS1} - V_{GS2} \rvert}{\Delta T}$	V_{DG} = 10 V, I_D = 200 µA, T_A = –55 to 125°C — SST404	20							µV/°C
		SST406	40							
		All U			10		25		80	
Common Mode Rejection Ratio	CMRR	V_{DG} = 10 to 20 V, I_D = 200 µA	102	95		95				dB

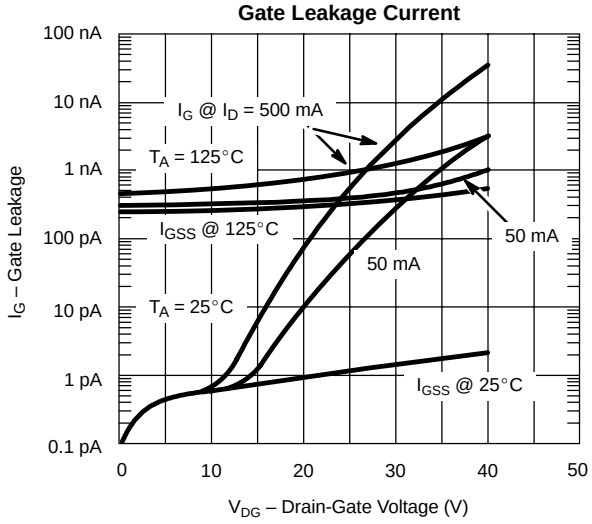
Notes
a. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing. NNR
b. Pulse test: PW ≤300 µs duty cycle ≤3%.

TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS OTHERWISE NOTED)

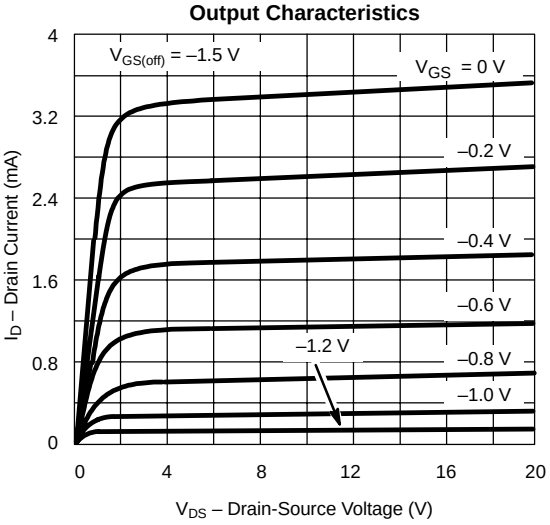
Drain Current and Transconductance vs. Gate-Source Cutoff Voltage



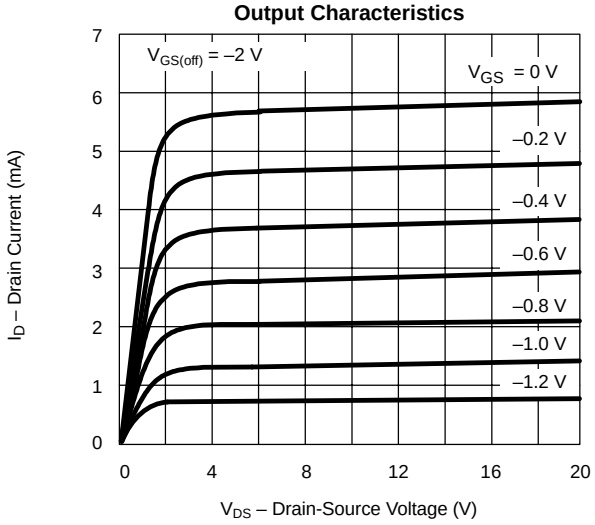
Gate Leakage Current



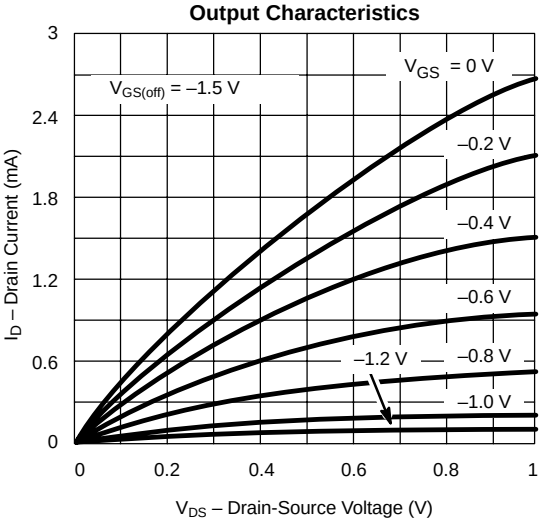
Output Characteristics



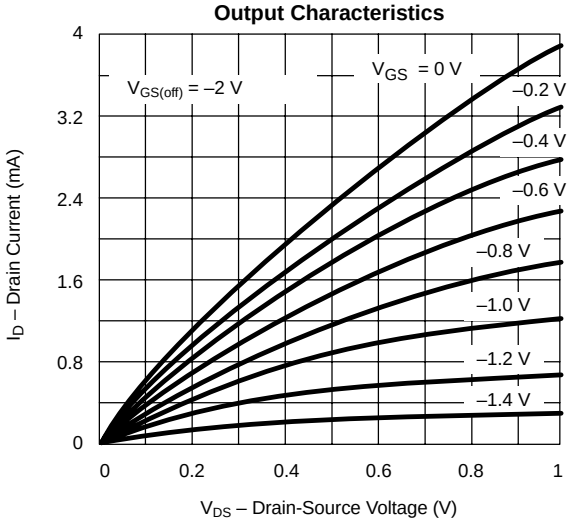
Output Characteristics



Output Characteristics

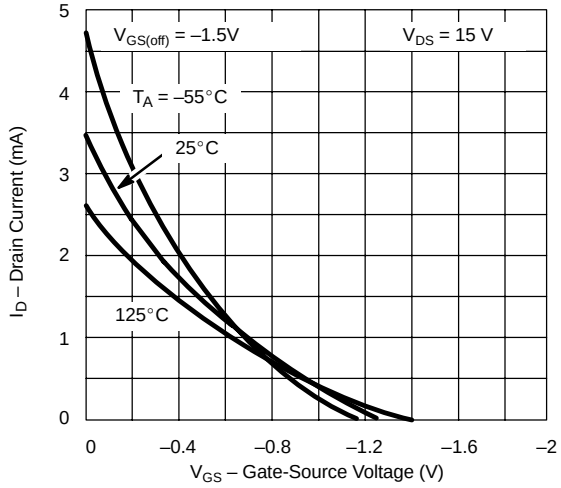


Output Characteristics

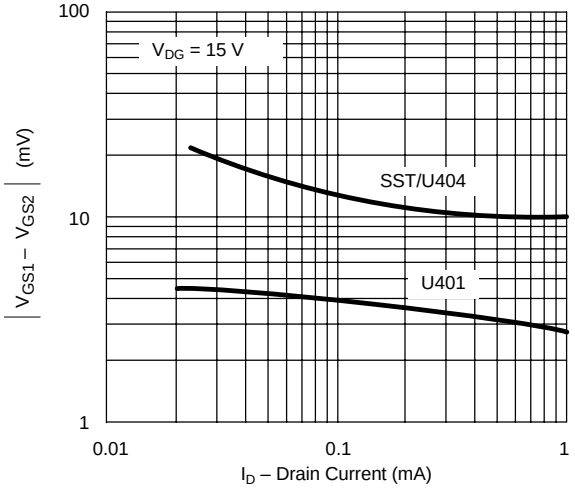


TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS OTHERWISE NOTED)

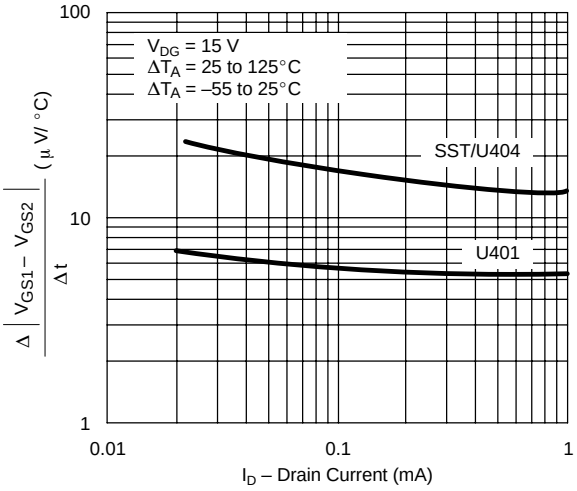
Transfer Characteristics



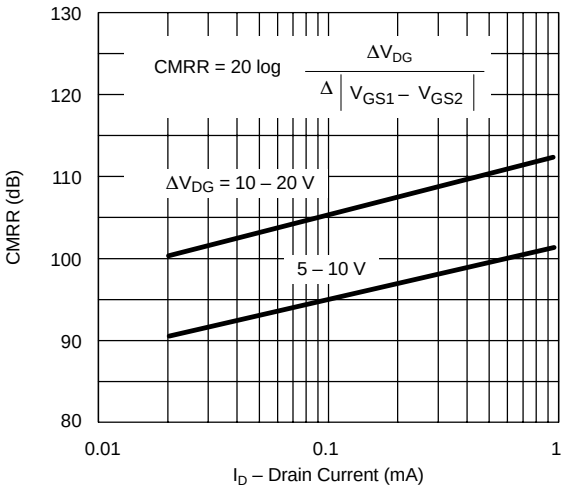
Gate-Source Differential Voltage vs. Drain Current



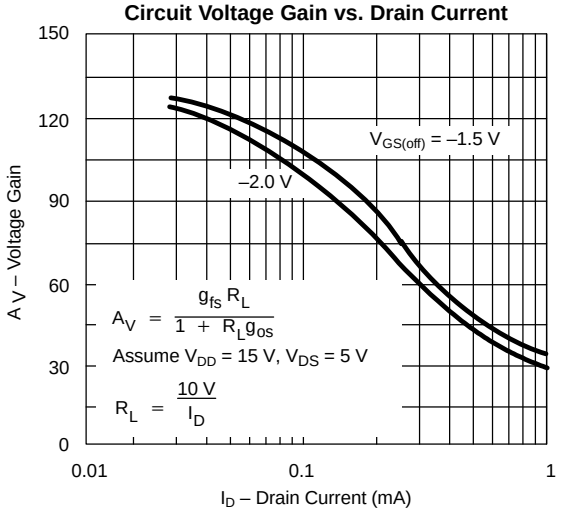
Voltage Differential with Temperature vs. Drain Current



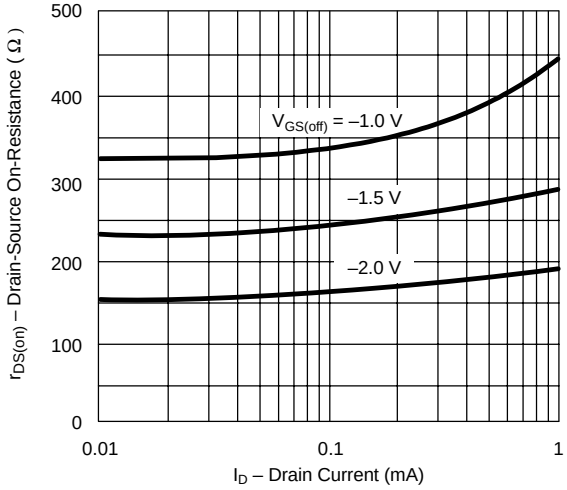
Common Mode Rejection Ratio vs. Drain Current



Circuit Voltage Gain vs. Drain Current



On-Resistance vs. Drain Current



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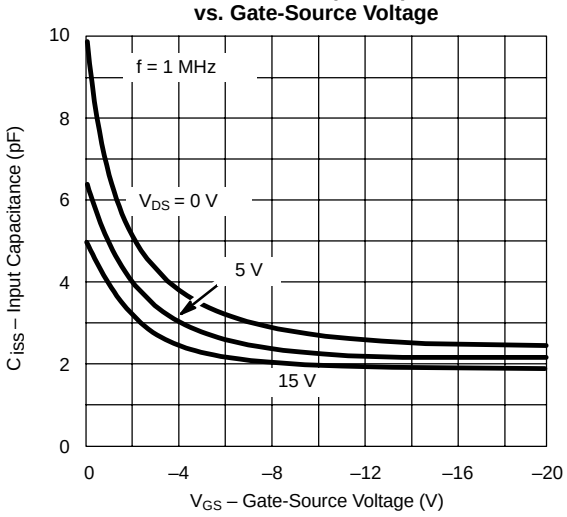
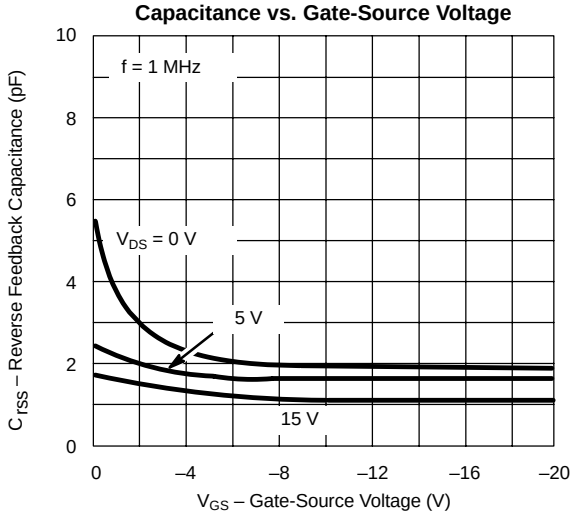
TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS OTHERWISE NOTED)

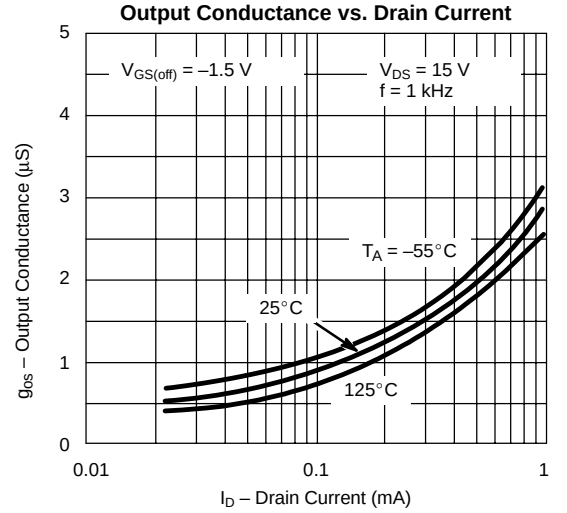
Common-Source Input Capacitance vs. Gate-Source Voltage



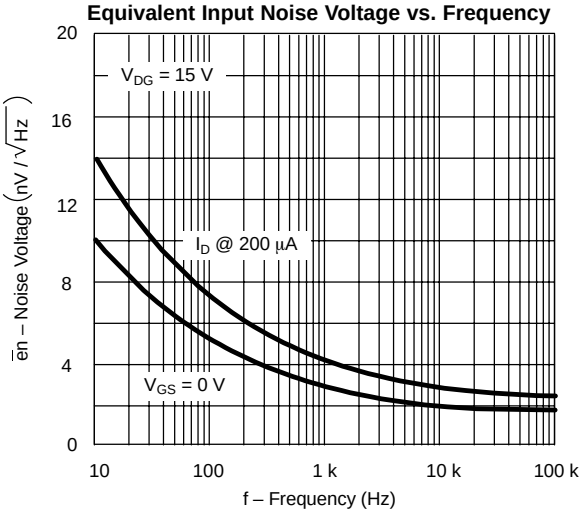
Common-Source Reverse Feedback Capacitance vs. Gate-Source Voltage



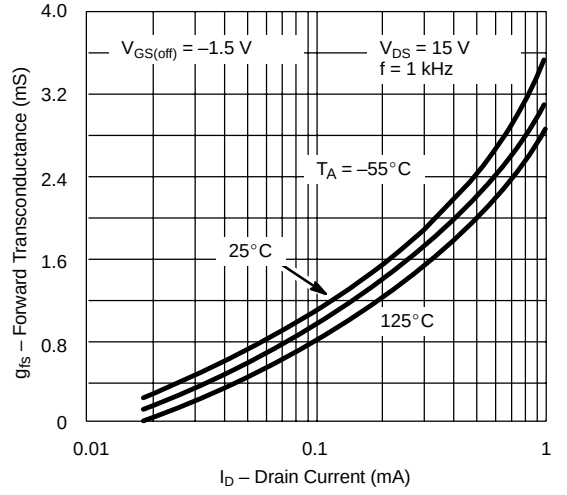
Output Conductance vs. Drain Current



Equivalent Input Noise Voltage vs. Frequency



Common-Source Forward Transconductance vs. Drain Current



On-Resistance and Output Conductance vs. Gate-Source Cutoff Voltage